



No.3023

2SA1703/2SC4483

PNP/NPN Epitaxial Planar Silicon Transistors

Low-Frequency Amp,
Electronic Governor Applications

Features

- Low collector-to-emitter saturation voltage.

() : 2SA1703

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)30	V
Collector to Emitter Voltage	V _{CE0}	(-)25	V
Emitter to Base Voltage	V _{EBO}	(-)5	V
Collector Current	I _C	(-)1.5	A
Collector Current(Pulse)	I _{CP}	(-)3	A
Collector Dissipation	P _C	1	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

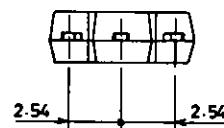
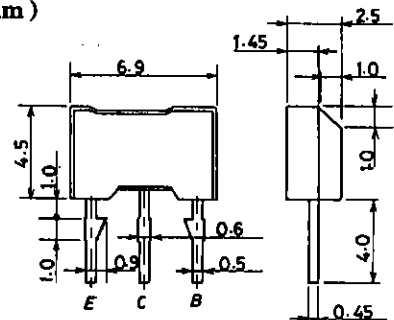
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = (-)20V, I _E = 0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0			(-)100	nA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)50mA	100*		400*	
			40			
Gain-Bandwidth Product	f _T	V _{CE} = (-)10V, I _C = (-)50mA		(180)150		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)500mA, I _B = (-)50mA	(-0.15)0.12		(-0.5)0.3	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = (-)500mA, I _B = (-)50mA	(-)0.9		(-)1.2	V
Output Capacitance	c _{ob}	V _{CB} = (-)10V, f = 1MHz		(25)15		pF
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = (-)10μA, I _E = 0	(-)30			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = (-)1mA, R _{BE} = ∞	(-)25			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = (-)10μA, I _C = 0	(-)5			V

* : The 2SA1703/2SC4483 are classified by 50mA h_{FE} as follows :

100 R 200	140 S 280	200 T 400
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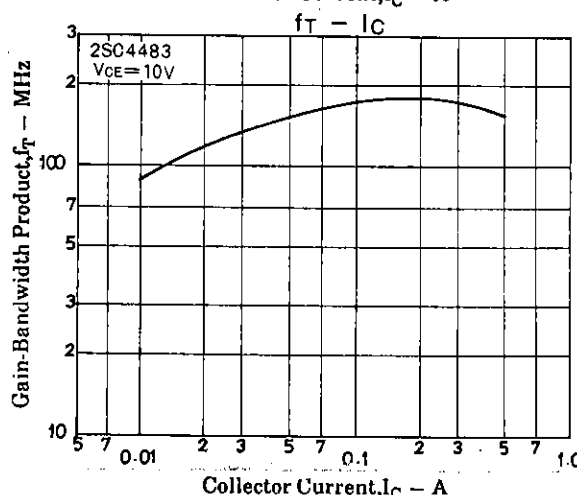
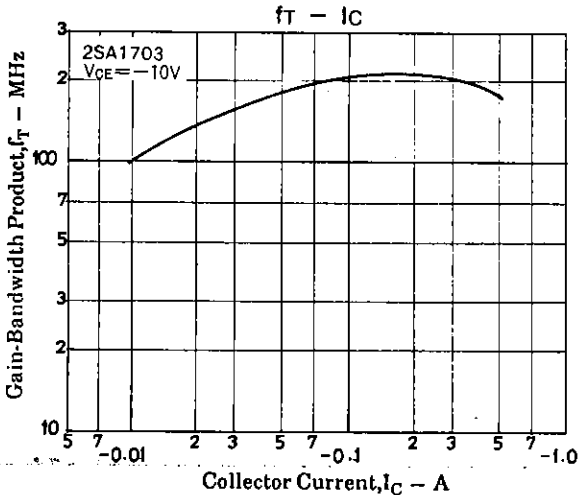
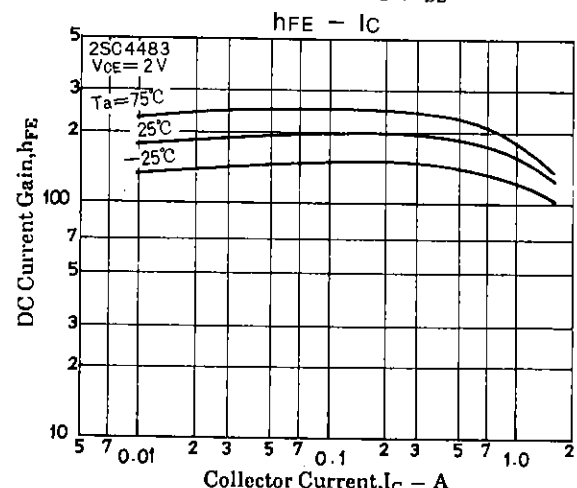
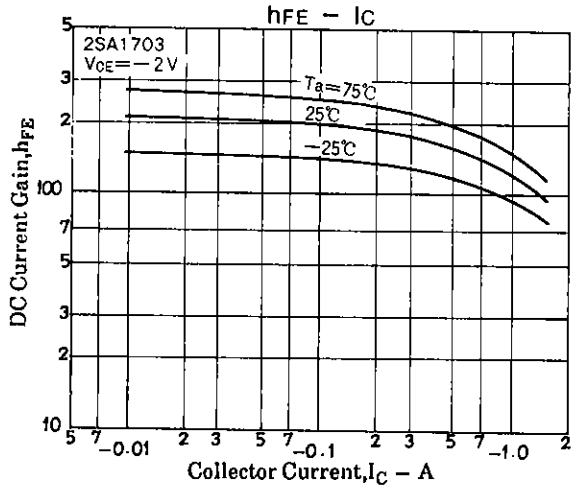
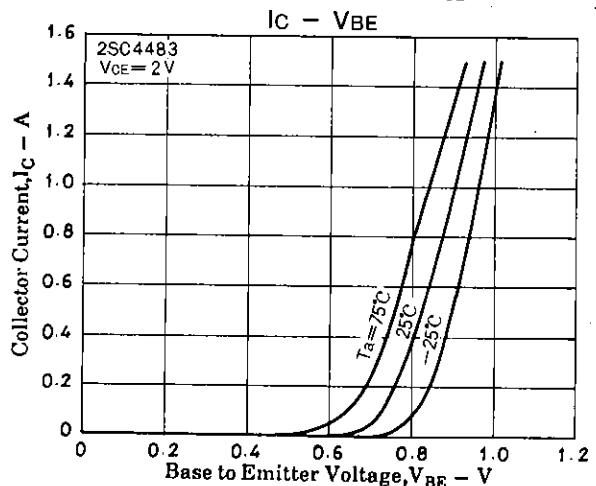
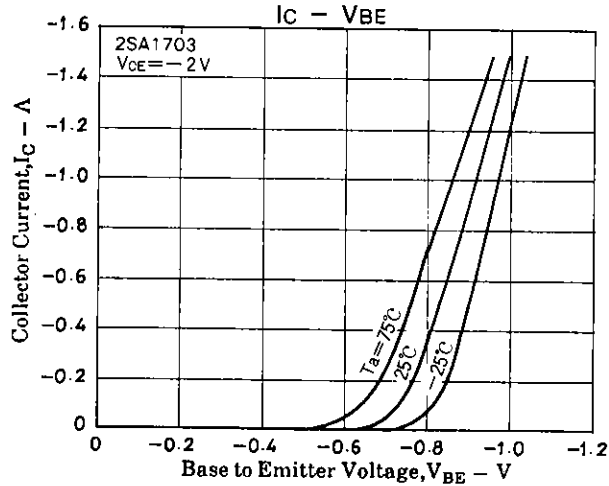
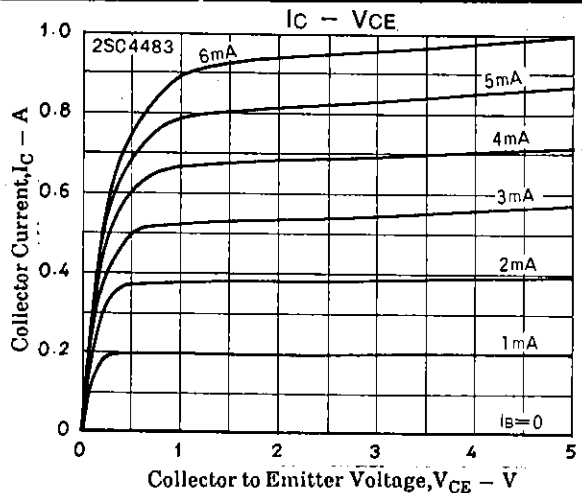
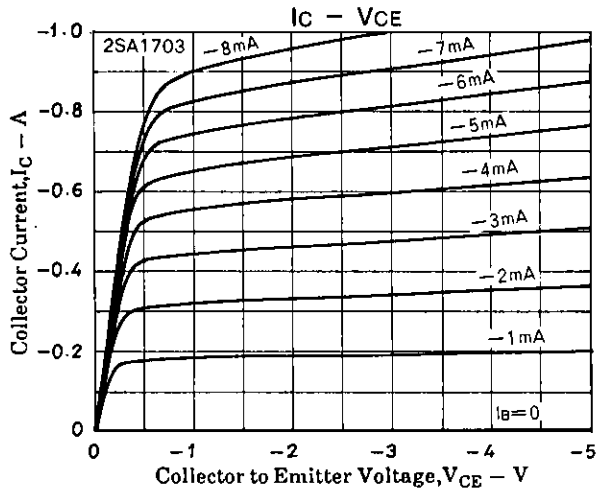
Package Dimensions 2064

(unit: mm)

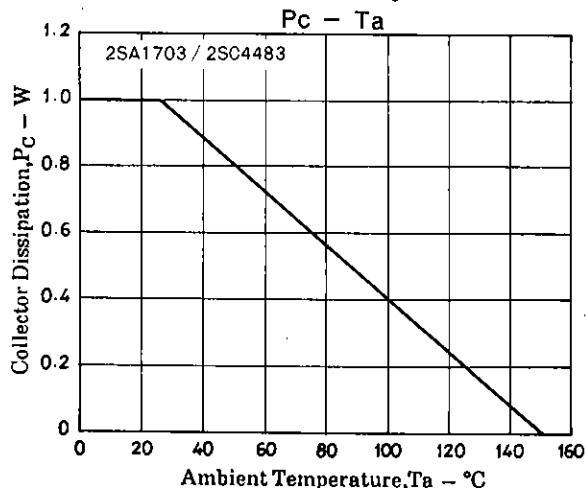
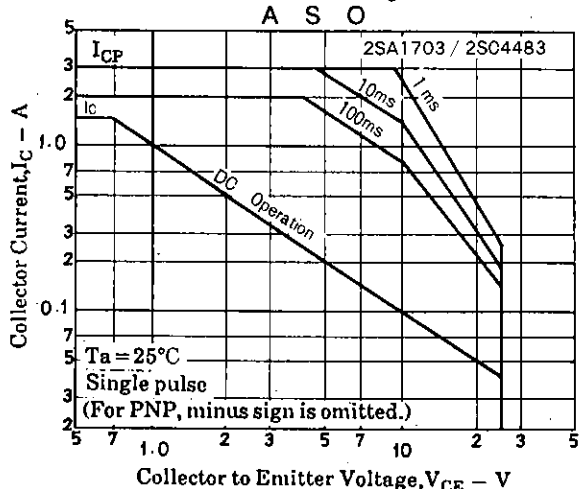
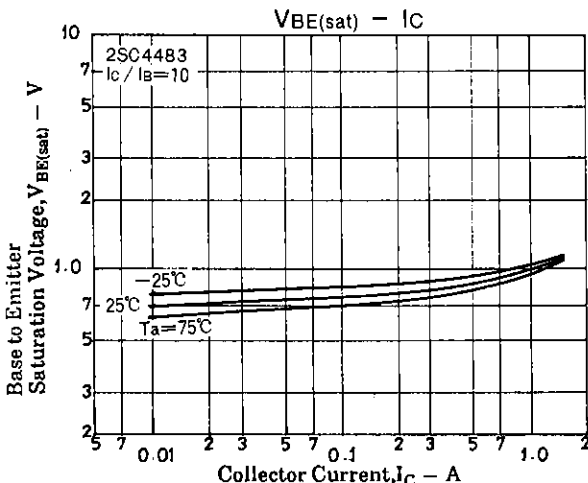
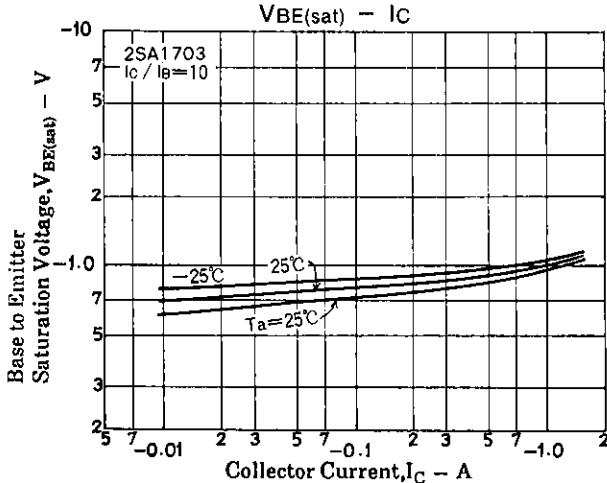
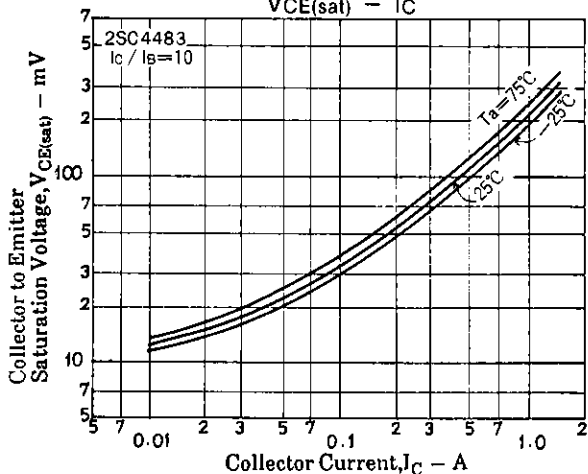
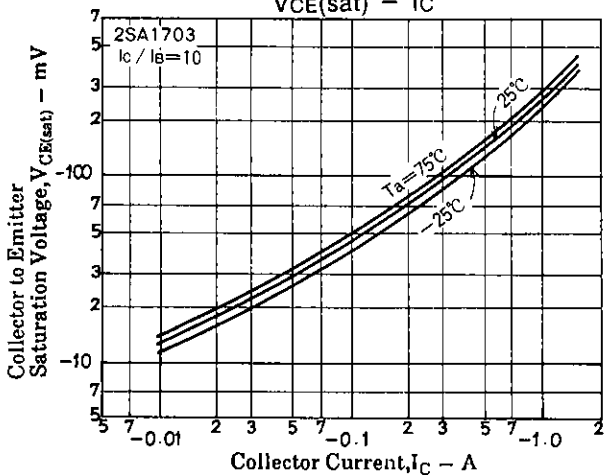
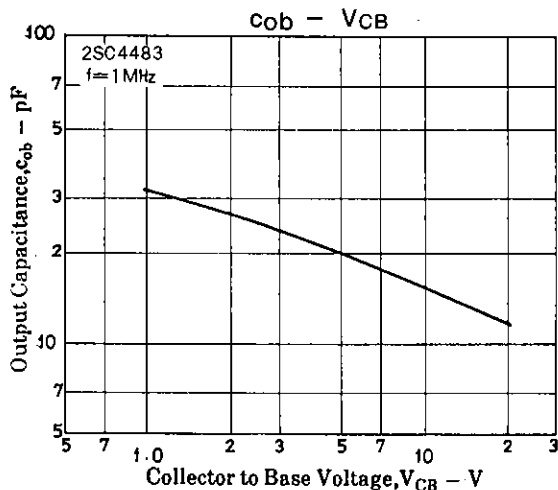
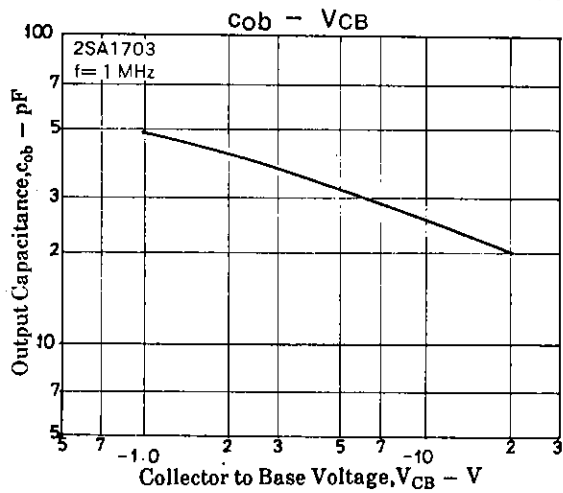


E: Emitter
C: Collector
B: Base
SANYO: NMP

2SA1703/2SC4483



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